Rev.F Apr.-2017

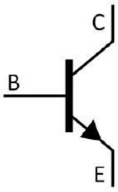
VRW056 ṂṂĿ QSQ ӕṀɥ s Ⅱ ヿ Silicon NPN transistor in a SOT-23 Plastic Package.

Hʋ ᵍ Ⅱ ڙ ͵ ↄ ḳ ṇ

Low C_{ob}.

[illegible]

High-frequency amplifier applications.

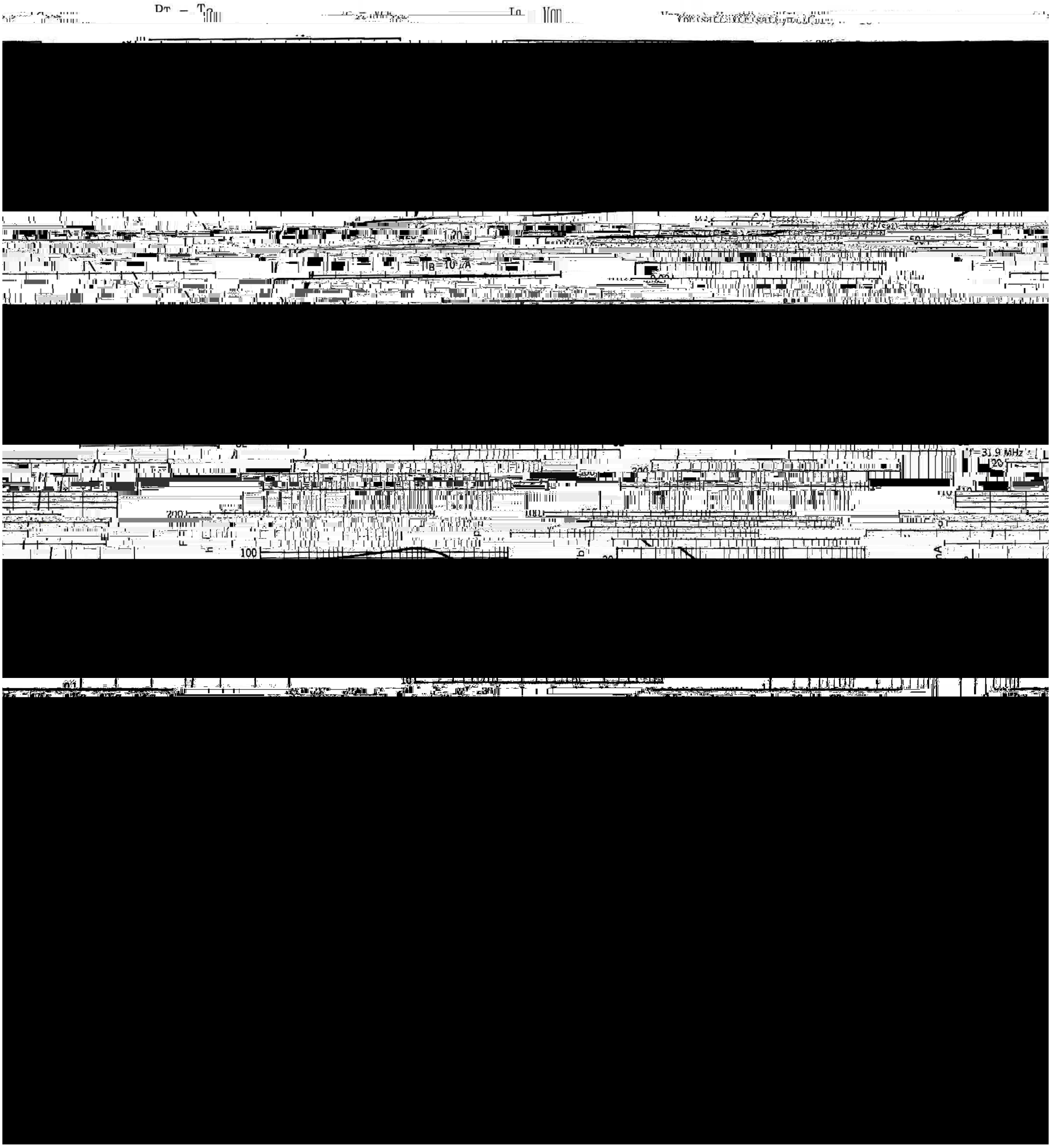


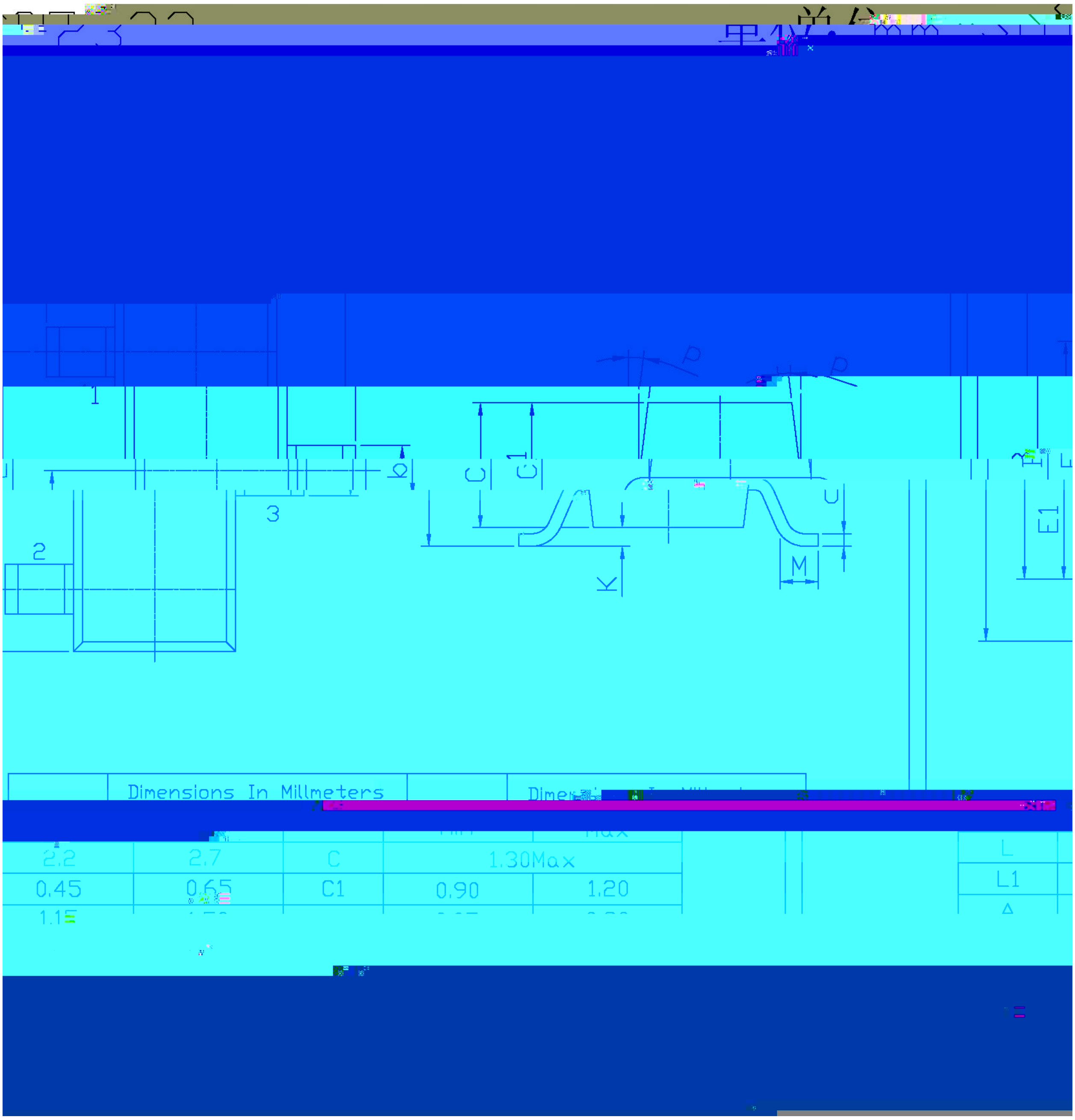
PIN1 χ Base PIN 2 χ Emitter PIN 3 χ Collector

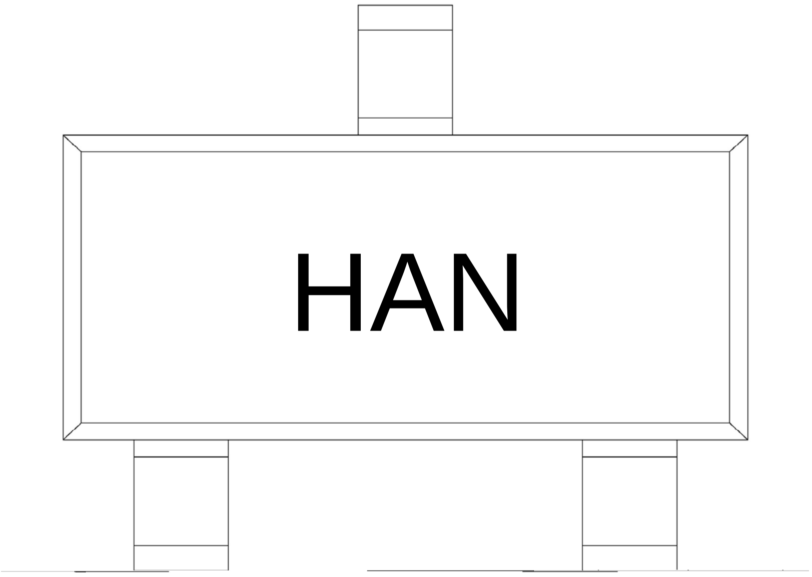
h_{FE} Classifications Symbol	N	P	Q
h_{FE} Range	56 120	82 180	120 270
Marking	HAN	HAP	HAQ

v ῍Ω̦ Parameter	˧ ᴺ Symbol	῍Ω̦Ӫ Rating	ᴅ Ʉ Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	50	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ῍Ω̦ Parameter	˧ ᴺ Symbol	╝ ⁏ᛚ ƫ Test Conditions	ῳ ṇ Ӫ Min	Ɛ ʒ Ӫ Typ	ῳ ᶼ Ӫ Max	ᴅ Ʉ Unit
Collector- Base Breakdown Voltage	V_{CBO}	I_C =50μA I_E=0	40			V
Collector-Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	25			V




1
2
3
P
P
C
C1
Q
U
K
M
E1
Dimensions In Millmeters
Max
2.2
2.7
C
1.30Max
0.45
0.65
C1
0.90
1.20
1.15
L
L1
Δ



ب ˝ χ

K χ　　ㅐ ƺ ᴎ Ͳɒ

D χ　　ㅐ ʒ ᴺ Ͳɒ

Q χ　　ㅐ h_{FE} ⁶ ₭Ͳɒ

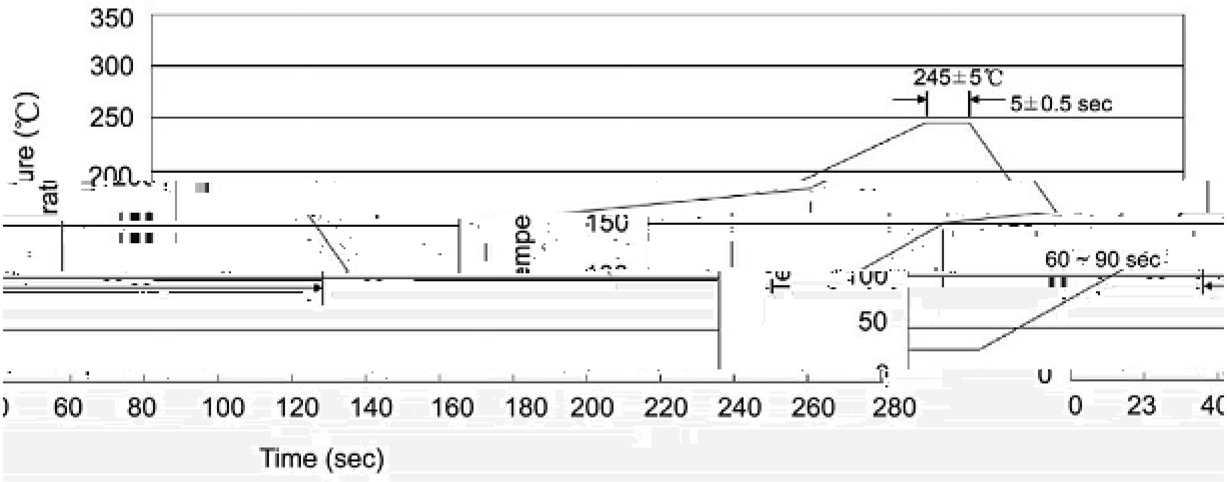
Note:

K χ　　Company Code

D χ　　Product Type Code

Q χ　　h_{FE} Classifications Symbol Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ	Note:
1 ỉ ♬ □ ỷ 25 Ḱ 150 ɬ ı ̀H ڙ 60 Ḱ 90sec;	1.Preheating:25~150 ɬ , Time:60~90sec.
2 Ś Ӫ □ ỷ 245 ° 5 ɬ ı ̀H ڙ ʿY ﾍ ĸѫ 5 ° 0.5sec;	2.Peak Temp.:245 ° 5 ɬ , Duration:5 ° 0.5sec.
3 ì ˙ ˥ ˛ ɔ ھ ỷ ĸѫ 2 Ḱ 10 ɬ /sec.	3. Cooling Speed: 2~10 ɬ /sec.

□ ỷ χ 260 ° 5 ɬ ̀H ڙ χ 10 ° 1 sec. Temp.:260 ° 5 ɬ Time:10 ° 1 sec

ɒ ̀ ɣ Ŀ / REEL

Package Type	Units					Dimension (unit mm^3)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205